IN THE CLAIMS:

Claim 1 (currently amended): An etchant, comprising:

hydrogen peroxide (H₂O₂); and

a mixed solution including at least one of an organic acid, an inorganic acid, and a neutral salt.

Claim 2 (original): The etchant according to claim 1, further comprising a hydrogen peroxide (H_2O_2) stabilizer.

Claim 3 (original): The etchant according to claim 1, wherein the etchant etches a double-layered metal layer that includes a copper (Cu) layer, and a molybdenum (Mo) layer.

Claim 4 (original): The etchant according to claim 1, wherein the etchant etches a double-layered metal layer that includes a copper (Cu) alloy layer, and a molybdenum (Mo) layer.

Claim 5 (canceled).

Claim 6 (canceled).

Claim 7 (currently amended): The etchant according to claim 1, wherein the neutral salt is selected from a group including the group consisting of potassium chloride (KCl), sodium chloride (NaCl), potassium hydrogen sulfate (KHSO₄), and potassium metaperiodate (KIO₄).

Claim 8 (currently amended): A method of forming an array substrate for use in a thin film transistor liquid crystal display (TFT-LCD) device, comprising:

forming a first metal layer on a substrate;

patterning the first metal layer to form a gate line and a gate electrode extended from the gate line;

forming a gate insulation layer on the substrate to cover the patterned first metal layer;

forming an active layer on the gate insulation layer and over the gate electrode;

forming an ohmic contact layer on the active layer;

forming a second metal layer on the gate insulation layer to cover the ohmic contact layer and the active layer;

forming a third copper metal layer on the second metal layer;

simultaneously patterning the second metal layer and the third <u>copper</u> metal layer to form a double-layered data line, a double-layered source electrode and a double-layered drain electrode using an etchant that includes hydrogen peroxide (H_2O_2) , a H_2O_2 stabilizer, and at least one of an organic acid, an inorganic acid and a neutral salt; and

forming a pixel electrode contacting the double-layered drain electrode.

Claim 9 (original): The method according to claim 8, wherein the first metal includes copper.

Claim 10 (original): The method according to claim 8, wherein the second metal includes molybdenum.

Claim 11 (canceled).

Claim 12 (currently amended): The method according to claim 8, wherein the third copper metal <u>layer</u> includes copper alloy.

Claim 13 (original) The method according to claim 8, wherein the double-layered data line, double-layered source electrode and double-layered drain electrode include a copper (Cu) layer and a molybdenum (Mo) layer.

Claim 14 (original): The method according to claim 8, wherein the double-layered data line, double-layered source electrode and double-layered drain electrode include a copper (Cu) alloy layer and a molybdenum (Mo) layer.

Claim 15 (original): The method according to claim 8, wherein the organic acid includes an acetic acid (CH₃COOH).

Claim 16 (currently amended): The method according to claim 8, wherein the inorganic acid is selected from a group including the group consisting of sulfuric acid (H₂SO₄), nitric acid (HNO₃), hydrochloric acid (HCl), and phosphoric acid (H₃PO₄).

Claim 17 (currently amended): The method according to claim 8, wherein the neutral salt is selected from a group including the group consisting of potassium chloride (KCl), sodium chloride (NaCl), potassium hydrogen sulfate (KHSO₄), and potassium metaperiodate (KIO₄).

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